

1 ABSTRACT OF THE DISCLOSURE

2 A semiconductor processing method of forming a plurality of
3 conductive lines includes, a) providing a substrate; b) providing a first
4 conductive material layer over the substrate; c) providing a first
5 insulating material layer over the first conductive layer; d) etching
6 through the first insulating layer and the first conductive layer to the
7 substrate to both form a plurality of first conductive lines from the first
8 conductive layer and provide a plurality of grooves between the first
9 lines, the first lines being capped by first insulating layer material, the
10 first lines having respective sidewalls; e) electrically insulating the first
11 line sidewalls; and f) after insulating the sidewalls, providing the
12 grooves with a second conductive material to form a plurality of second
13 lines within the grooves which alternate with the first lines. Integrated
14 circuitry formed according to the method, and other methods, is also
15 disclosed.

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